

Abstract

Disclosed is a method for forming a fine pattern of a semiconductor device in which the spacing between neighboring lines is reduced to be less than the resolution limit of a lithographic process. The method includes the steps of: (a) sequentially forming a base layer to be patterned, a lower photoresist layer, a blocking layer and an upper photoresist layer on a substrate; (b) forming the first photoresist pattern on the upper photoresist layer, and etching the blocking layer according to the first photoresist pattern; (c) forming the second photoresist pattern on the lower photoresist layer, which is opened by the spacing of the first photoresist pattern, wherein the spacing of the first photoresist pattern is greater than a line width of the second photoresist pattern; (d) etching the base layer using the second photoresist pattern as a mask; and (e) stripping the remaining photoresist layer.